Transistors

# 10V Drive Nch MOSFET

## **R5007ANJ**

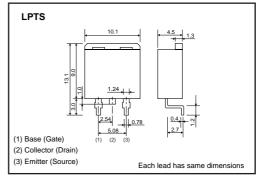
## Structure

Silicon N-channel MOSFET

#### Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Wide SOA (safe operating area).
- 4) Gate-source voltage (VGSS)
- guaranteed to be  $\pm 30$ V.
- 5) Drive circuits can be simple.
- 6) Parallel use is easy.

## •Dimensions (Unit : mm)



## Applications

Switching

#### Packaging specifications

	3 3 1	
	Package	Taping
	Code	TL
Туре	Basic ordering unit (pieces)	1000
R5007	0	

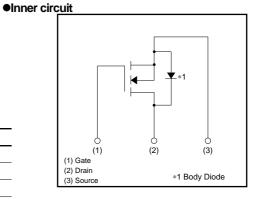
## •Absolute maximum ratings (Ta=25°C)

Parameter	Symbol		Limits	Unit	
Drain-source voltage	Vdss		500	V	
Gate-source voltage	Vgss		±30	V	
Drain current	Continuous	lo	*3	±7	А
Drain current	Pulsed	Idp	*1	±28	А
Source current	Continuous	ls	*3	7	А
(Body Diode)	Pulsed	Isp	*1	28	A
Avalanche Current		las	*2	3.5	А
Avalanche Energy	Eas	*2	3.5	mJ	
Total power dissipation	P⊳		40	W	
Channel temperature	Tch		150	°C	
Range of storage tem	Tstg		-55 to +150	°C	

\*1 Pw≤10µs, Duty cycle≤1%
 \*2 L≒ 500µH, V<sub>DD</sub>=50V, Rg=25Ω, Starting, Tch=25°C
 \*3 Limited only by maximum tempterature allowed

#### Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to case	Rth(ch-c)	3.13	°C/W





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## ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Gate-source leakage	lgss	-	_	±100	nA	Vgs=±30V, Vds=0V	
Drain-source breakdown voltage	V(BR)DSS	500	_	-	V	ID=1mA, VGs=0V	
Zero gate voltage drain current	IDSS	-	_	100	μΑ	Vds=500V, Vgs=0V	
Gate threshold voltage	VGS(th)	2.5	_	4.5	V	Vos=10V, Io=1mA	
Static drain-source on-state resistance	RDS(on)*	-	0.8	1.05	Ω	ID=3.5A, VGs=10V	
Forward transfer admittance	Y <sub>fs</sub>   *	2.5	_	-	S	ID=3.5A, VDS=10V	
Input capacitance	Ciss	-	500	_	pF	Vds=25V	
Output capacitance	Coss	-	300	_	pF	Vgs=0V	
Reverse transfer capacitance	Crss	-	23	-	pF	f=1MHz	
Turn-on delay time	td(on) *	-	20	-	ns	Id=3.5A, Vdd≒250V	
Rise time	tr *	-	22	-	ns	Vgs=10V	
Turn-off delay time	td(off) *	-	50	_	ns	R∟=71.4Ω	
Fall time	tr *	_	25	_	ns	Rg=10Ω	
Total gate charge	Qg *	_	13	-	nC	Vdd≒250V	
Gate-source charge	Qgs *	-	3.5	-	nC	ID=7A Vgs=10V	
Gate-drain charge	Q <sub>gd</sub> *	_	5.5	_	nC	RL=35.7Ω / RG=10Ω	

\* Pulsed

## •Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd *	-	-	1.5	V	Is= 7A, V <sub>GS</sub> =0V

\* Pulsed

## Transistors

## •Switching characteristics measurement circuit

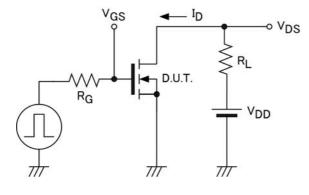


Fig.1 Switching time measurement circuit

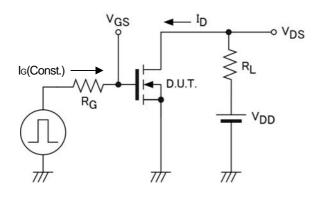


Fig.3 Gate charge measurement circuit

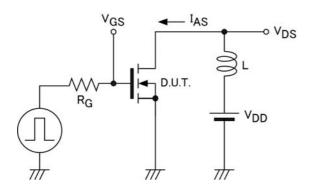


Fig.5 Avalanche measurement circuit

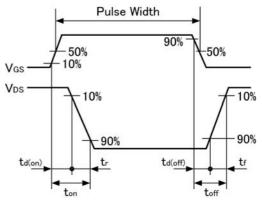
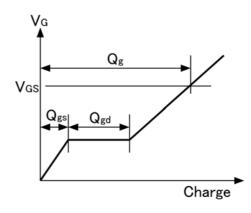
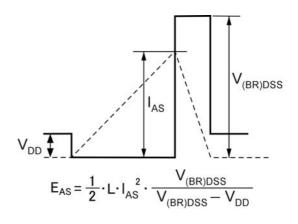


Fig.2 Switching waveforms









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Appendix1-Rev2.0

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